

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1. (Previously Presented) A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer and a third conductive layer being in contact with said gate insulating film, side surfaces of the first conductive layer and top and side surfaces of said second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 2. (Previously Presented). A ferroelectric liquid crystal display device according to claim 1, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise

a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 3. (Previously Presented). A ferroelectric liquid crystal display device according to claim 1, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 4. (Previously Presented). A ferroelectric liquid crystal display device according to claim 1, wherein said third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 5. (Canceled).

Claim 6. (Previously Presented) A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer and a third conductive layer being in contact with said gate insulating film, side surfaces of said first conductive layer and top and side surfaces of said second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region

and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said third conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 7. (Previously Presented). A ferroelectric liquid crystal display device according to claim 6, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 8. (Previously Presented). A ferroelectric liquid crystal display device according to claim 6, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 9. (Previously Presented). A ferroelectric liquid crystal display device according to claim 6, wherein said third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W),

and molybdenum (Mo).

Claim 10. (Canceled).

Claim 11. (Currently amended) A ferroelectric liquid crystal display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode and a second gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a pair of LDD regions and first source and drain regions;

wherein said second gate electrode partially overlaps said pair of LDD regions while said first gate electrode does not overlap said pair of LDD regions, and

wherein said second gate electrode comprises a different material from said first gate electrode, and

said p-channel TFT comprising:

a third gate electrode and a fourth gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film interposed therebetween, said second semiconductor layer comprising a second channel formation region and second source and drain regions being in contact with said second channel formation region,

wherein said fourth gate electrode partially overlaps said second source and drain regions while the third gate electrode does not overlap said second source and drain regions,

wherein said fourth gate electrode comprises a different material from said third gate

electrode, and

wherein a wiring is connected to at least one of said second source and drain regions.

Claim 12. (Previously Presented). A ferroelectric liquid crystal display device according to claim 11, wherein said first to fourth gate electrodes comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 13. (Canceled).

Claim 14. (Currently amended) A goggle type ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer, and a third conductive layer being in contact with said gate insulating film, side surfaces of said first conductive layer and top and side surfaces of said second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said p-channel TFT is partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 15. (Previously Presented). A goggle type display device according to claim 14, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 16. (Previously Presented). A goggle type display device according to claim 14, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 17. (Previously Presented). A goggle type display device according to claim 14, wherein said third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 18. (Canceled).

Claim 19. (Currently amended) A goggle type ferroelectric liquid crystal display device

having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, a second conductive layer being in contact with said first conductive layer, and a third conductive layer being in contact with said gate insulating film, side surfaces of said first conductive layer and top and side surfaces of said second conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein said second conductive layer comprises a different material from said first conductive layer;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said third conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said third conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 20. (Previously Presented). A goggle type display device according to claim 19, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a

material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 21. (Previously Presented). A goggle type display device according to claim 19, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 22. (Previously Presented). A goggle type display device according to claim 19, wherein said third conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 23. (Canceled).

Claim 24. (Currently Amended) A goggle type ferroelectric liquid crystal display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode and a second gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a pair of LDD regions and first source and drain regions;

wherein said second gate electrode partially overlaps said pair of LDD regions while said first gate electrode does not overlap said pair of LDD regions, and

wherein said second gate electrode comprises a different material from said first gate electrode, and

said p-channel TFT comprising:

a third gate electrode and a fourth gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film interposed therebetween, said second semiconductor layer comprising a second channel formation region and second source and drain regions being in contact with said second channel formation region,

wherein said fourth gate electrode partially overlaps said second source and drain regions while said third gate electrode does not overlap said second source and drain regions,

wherein said fourth gate electrode comprises a different material from said third gate electrode, and

wherein a wiring is connected to [[said]] at least one of said second source and drain regions.

Claim 25. (Previously presented). A goggle type display device according to claim 24, wherein said first to fourth gate electrodes comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 26. (Canceled).